TOSHIBA

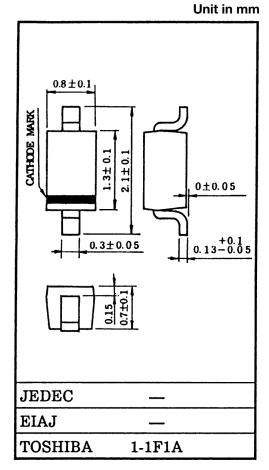
Variable Capacitance Diode

Silicon Epitaxial Planar Type

VCO For UHF Ratio

Features

- Ultra Low Series Resistance : $r_s = 0.2 \Omega$ (Typ.) Useful for Small Size Set



Absolute Maximum Ratings (Ta = 25°C)

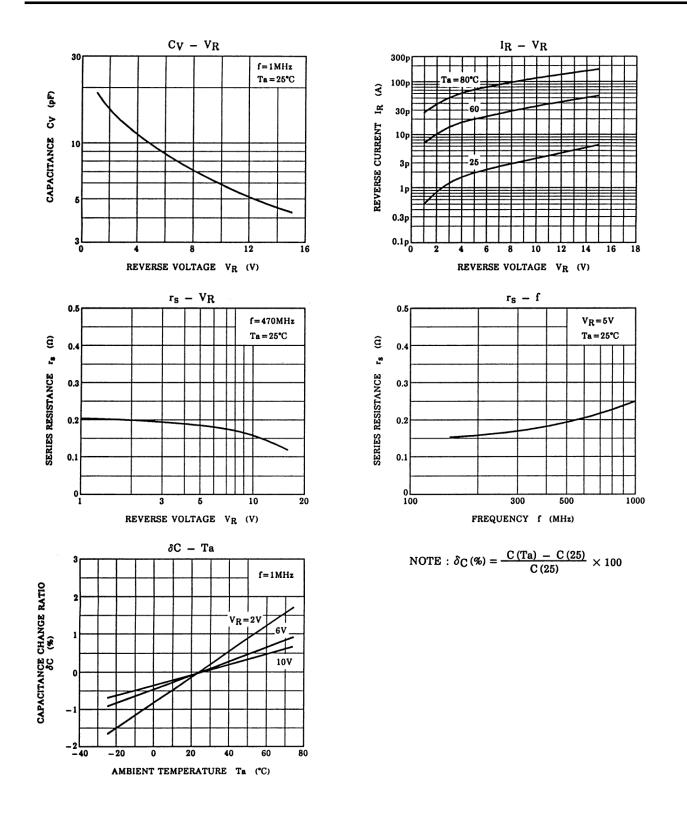
Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V _R	15	V
Junction Temperature	Tj	125	°C
Storage Temperature Range	T _{stg}	-55 ~ 125	°C

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V _R	I _R = 1µA	15	-	-	V
Reverse Current	I _R	V _R = 15V	-	-	3	nA
Capacitance	C2V	$V_{R} = 2V$, f = 1MHz	14	15	16	pF
Capacitance	C10V	V _R = 10V, f = 1MHz	5.5	6	6.5	pF
Capacitance Ratio	C2V/C10V	-	2.0	2.5	-	-
Series Resistance	r _s	V _R = 5V, f = 470MHz	-	0.2	0.4	Ω

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